

# ESDBL6V8BP

## Silicon Epitaxial Planar Diode

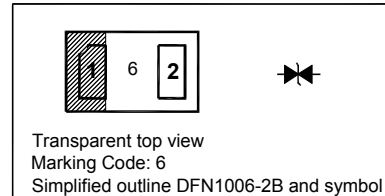
ESD protection diode

### Features

- Ultra small mold type
- Bi-direction high reliability

### PINNING

PIN	DESCRIPTION
1	Anode
2	Anode

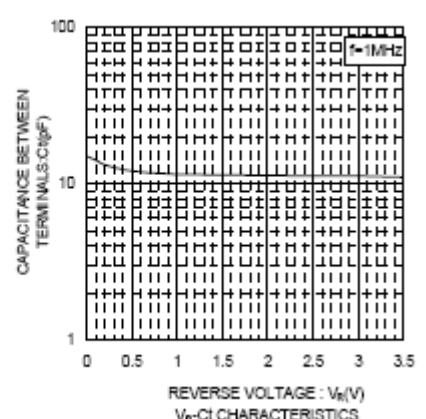
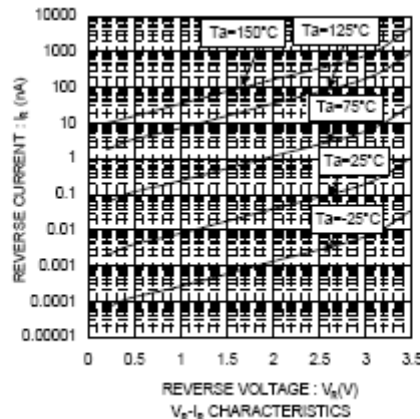
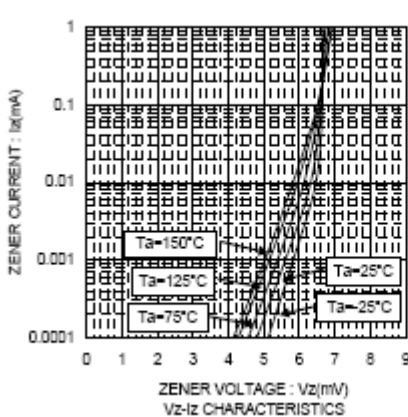


### Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Peak Pulse Power ( $t_p = 10 \times 1000 \mu\text{s}$ )	$P_{PK}$	10	W
Power Dissipation	$P_D$	100	mW
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 55 to + 150	$^\circ\text{C}$
Operation Temperature Range	$T_{opr}$	- 55 to + 150	$^\circ\text{C}$

### Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
Zener Voltage at $I_Z = 1 \text{ mA}$	$V_Z$	5.78	-	7.82	V
Reverse Current at $V_R = 3.5 \text{ V}$	$I_R$	-	-	0.5	$\mu\text{A}$
Capacitance between Terminals at $V_R = 0 \text{ V}$ , $f = 1 \text{ MHz}$	$C_T$	-	32	-	pF



TOP DYNAMIC

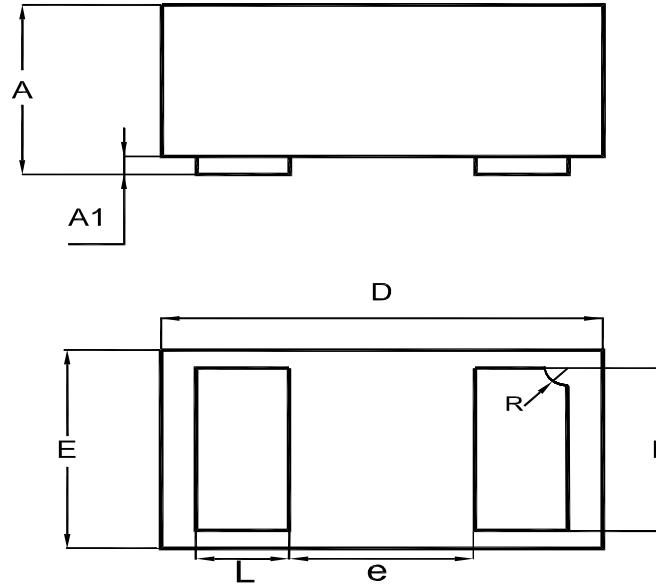


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## PACKAGE OUTLINE

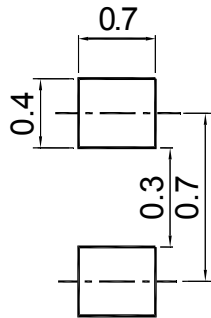
Plastic surface mounted package; 2 leads

DFN1006-2B



UNIT	A	A1	b	D	E	e	L	R
mm	0.40	0.05	0.55	1.05	0.65	0.4	0.3	0.15
	0.36	0	0.45	0.95	0.55		0.2	0.05

## Recommended Soldering Footprint



## Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
DFN1006-2B	8	4 ± 0.1	0.157 ± 0.004	178	7	5,000

**TOP DYNAMIC**



Dated: 07/07/2014 Rev: 01